

# MOS FIELD EFFECT POWER TRANSISTORS

## 2SK2724

### SWITCHING

### N-CHANNEL POWER MOS FET

### INDUSTRIAL USE

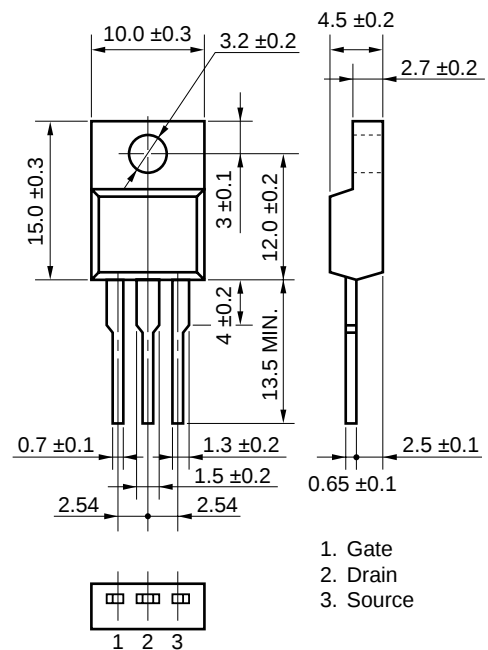
#### DESCRIPTION

This product is N-Channel MOS Field Effect Transistor designed for high current switching applications.

#### FEATURES

- Low On-Resistance  
 $R_{DS(on)1} = 27 \text{ m}\Omega \text{ Max. (} V_{GS} = 10 \text{ V, } I_D = 18 \text{ A)}$   
 $R_{DS(on)2} = 40 \text{ m}\Omega \text{ Max. (} V_{GS} = 4 \text{ V, } I_D = 18 \text{ A)}$
- Low  $C_{iss}$   $C_{iss} = 1\ 200 \text{ pF Typ.}$
- Built-in G-S Protection Diode
- Isolated TO-220 package

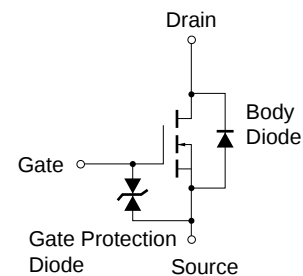
#### PACKAGE DIMENSIONS (in millimeter)



#### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ )

|                                                      |                |             |                  |
|------------------------------------------------------|----------------|-------------|------------------|
| Drain to Source Voltage                              | $V_{DSS}$      | 60          | V                |
| Gate to Source Voltage                               | $V_{GSS}$      | $\pm 20$    | V                |
| Drain Current (DC)                                   | $I_{D(DC)}$    | $\pm 35$    | A                |
| Drain Current (Pulse)*                               | $I_{D(pulse)}$ | $\pm 140$   | A                |
| Total Power Dissipation ( $T_A = 25^\circ\text{C}$ ) | $P_T$          | 2.0         | W                |
| Total Power Dissipation ( $T_C = 25^\circ\text{C}$ ) | $P_T$          | 30          | W                |
| Channel Temperature                                  | $T_{ch}$       | 150         | $^\circ\text{C}$ |
| Storage Temperature                                  | $T_{stg}$      | -55 to +150 | $^\circ\text{C}$ |

#### MP-45F (ISOLATED TO-220)



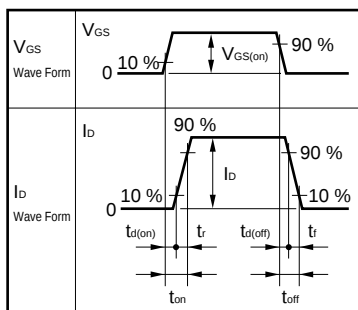
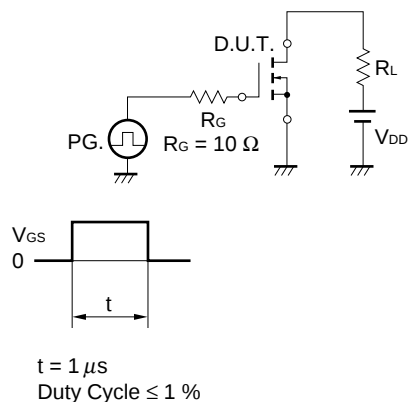
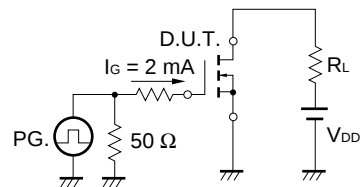
\*  $PW \leq 10 \mu\text{s}$ , duty cycle  $\leq 1\%$

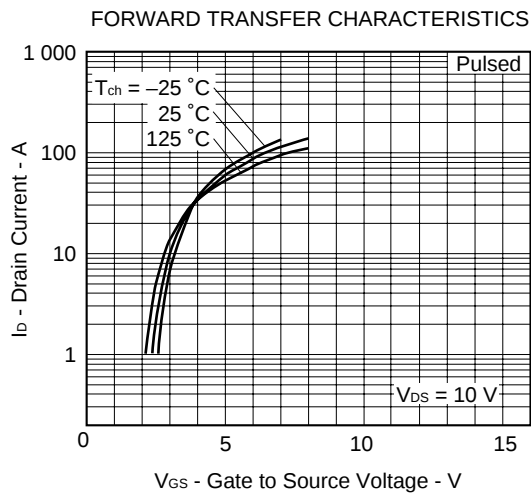
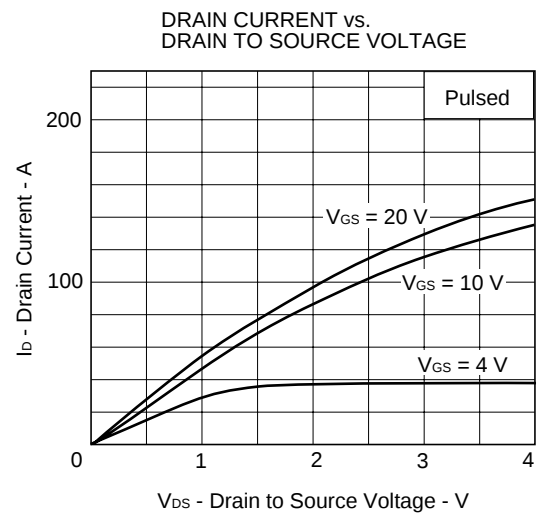
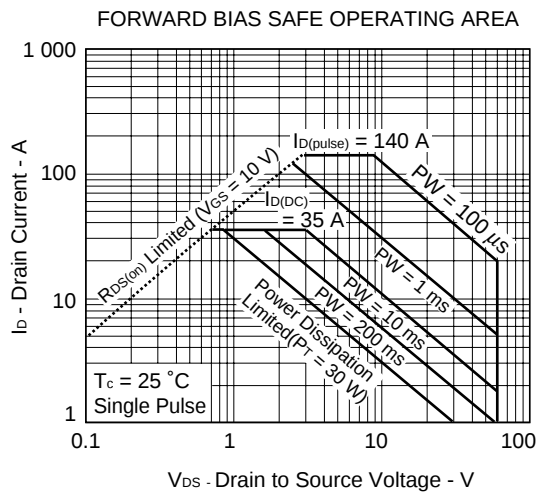
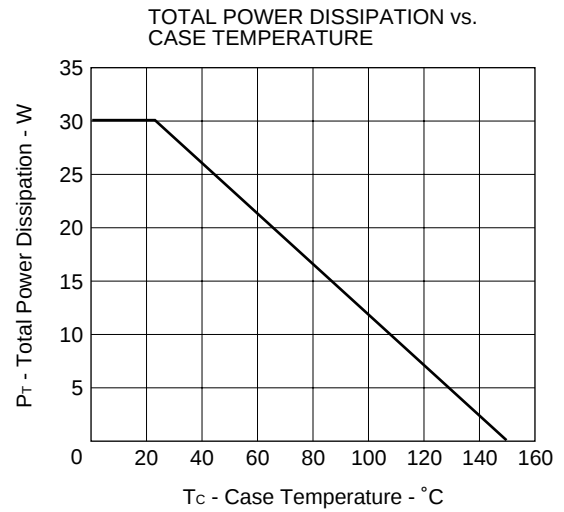
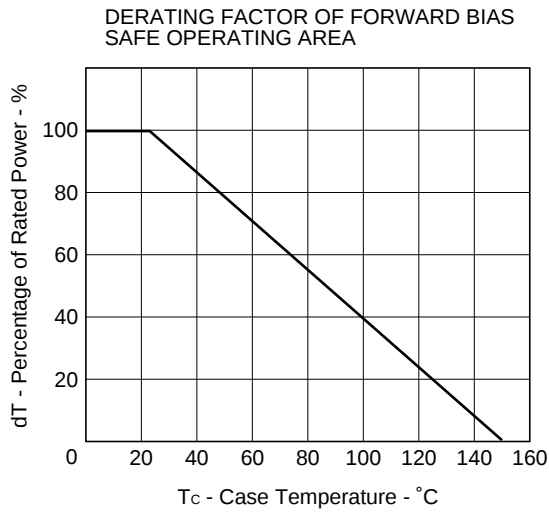
The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if voltage exceeding the rated voltage may be applied to this device.

The information in this document is subject to change without notice.

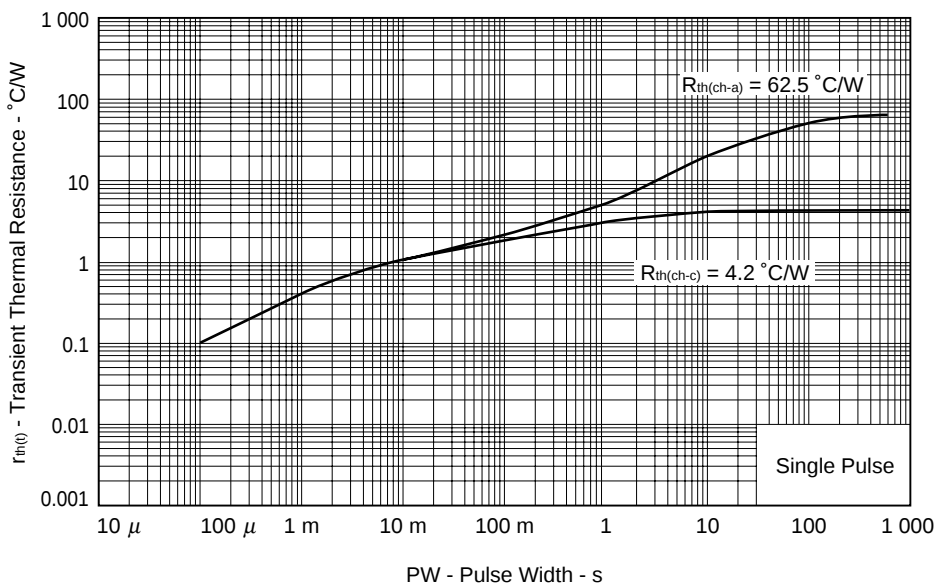
**ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C)**

| CHARACTERISTIC                      | SYMBOL               | TEST CONDITION                                                                                            | MIN. | TYP.  | MAX. | UNIT |
|-------------------------------------|----------------------|-----------------------------------------------------------------------------------------------------------|------|-------|------|------|
| Drain to Source On-State Resistance | R <sub>DS(on)1</sub> | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 18 A                                                             |      | 20    | 27   | mΩ   |
|                                     | R <sub>DS(on)2</sub> | V <sub>GS</sub> = 4 V, I <sub>D</sub> = 18 A                                                              |      | 33    | 40   | mΩ   |
| Gate to Source Cutoff Voltage       | V <sub>GS(off)</sub> | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA                                                             | 1.0  | 1.5   | 2.0  | V    |
| Forward Transfer Admittance         | y <sub>fs</sub>      | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 18 A                                                             | 10   | 23    |      | S    |
| Drain Leakage Current               | I <sub>DSS</sub>     | V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0                                                               |      |       | 10   | μA   |
| Gate to Source Leakage Current      | I <sub>GSS</sub>     | V <sub>GS</sub> = ±20 V, V <sub>DS</sub> = 0                                                              |      |       | ±10  | μA   |
| Input Capacitance                   | C <sub>iss</sub>     | V <sub>DS</sub> = 10 V,<br>V <sub>GS</sub> = 0,<br>f = 1 MHz                                              |      | 1 200 |      | pF   |
| Output Capacitance                  | C <sub>oss</sub>     |                                                                                                           |      | 570   |      | pF   |
| Reverse Transfer Capacitance        | C <sub>rss</sub>     |                                                                                                           |      | 270   |      | pF   |
| Turn-On Delay Time                  | t <sub>d(on)</sub>   | I <sub>D</sub> = 18 A,<br>V <sub>GS(on)</sub> = 10 V,<br>V <sub>DD</sub> = 30 V,<br>R <sub>G</sub> = 10 Ω |      | 35    |      | ns   |
| Rise Time                           | t <sub>r</sub>       |                                                                                                           |      | 280   |      | ns   |
| Turn-Off Delay Time                 | t <sub>d(off)</sub>  |                                                                                                           |      | 160   |      | ns   |
| Fall Time                           | t <sub>f</sub>       |                                                                                                           |      | 170   |      | ns   |
| Total Gate Charge                   | Q <sub>G</sub>       | I <sub>D</sub> = 35 A,<br>V <sub>DD</sub> = 48 V,<br>V <sub>GS</sub> = 10 V                               |      | 50    |      | nC   |
| Gate to Source Charge               | Q <sub>GS</sub>      |                                                                                                           |      | 5.0   |      | nC   |
| Gate to Drain Charge                | Q <sub>GD</sub>      |                                                                                                           |      | 22    |      | nC   |
| Body Diode Forward Voltage          | V <sub>F(S-D)</sub>  | I <sub>F</sub> = 35 A, V <sub>GS</sub> = 0                                                                |      | 1.0   |      | V    |
| Reverse Recovery Time               | t <sub>rr</sub>      | I <sub>F</sub> = 35 A, V <sub>GS</sub> = 0,<br>di/dt = 100 A/μs                                           |      | 70    |      | ns   |
| Reverse Recovery Charge             | Q <sub>rr</sub>      |                                                                                                           |      | 130   |      | nC   |

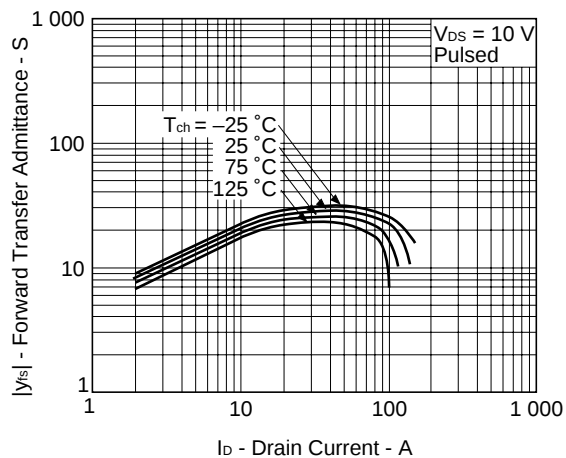
**Test Circuit 1 Switching Time****Test Circuit 2 Gate Charge**



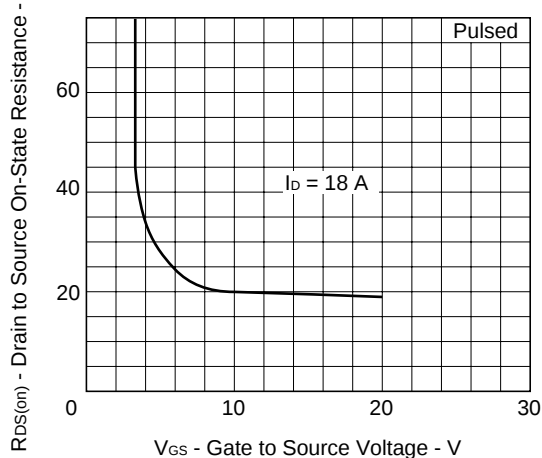
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



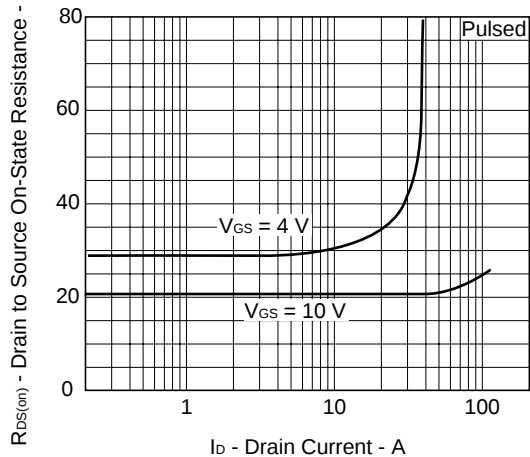
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



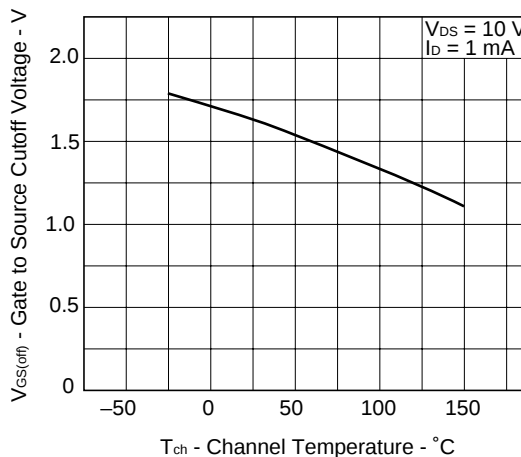
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE

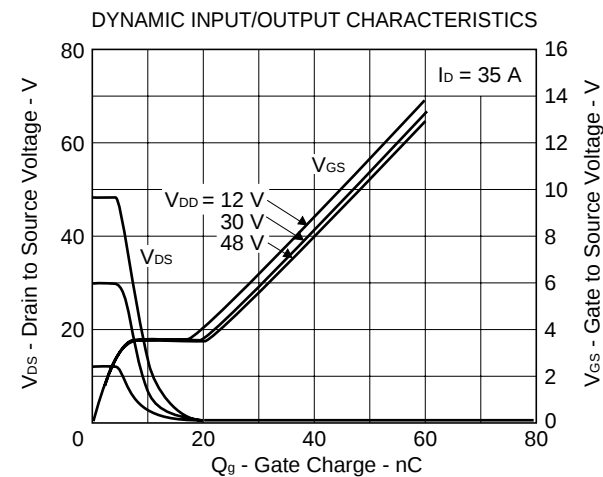
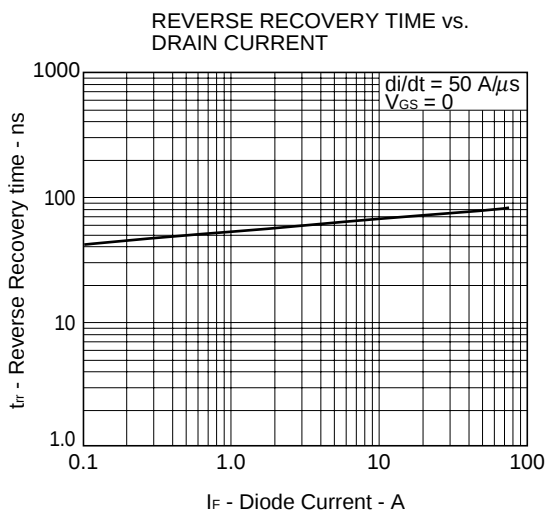
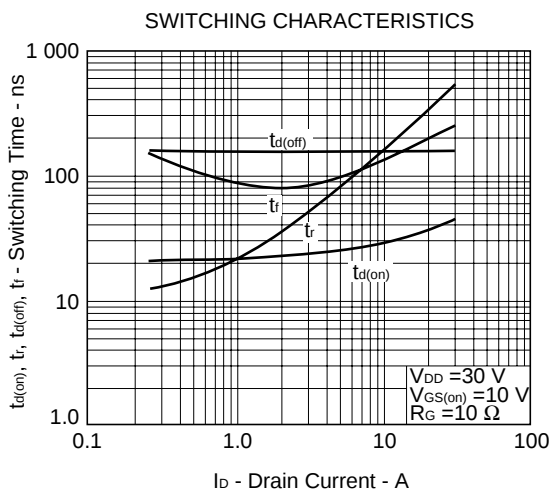
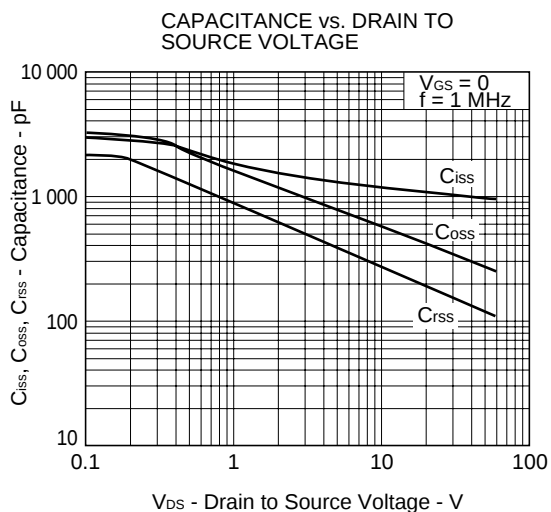
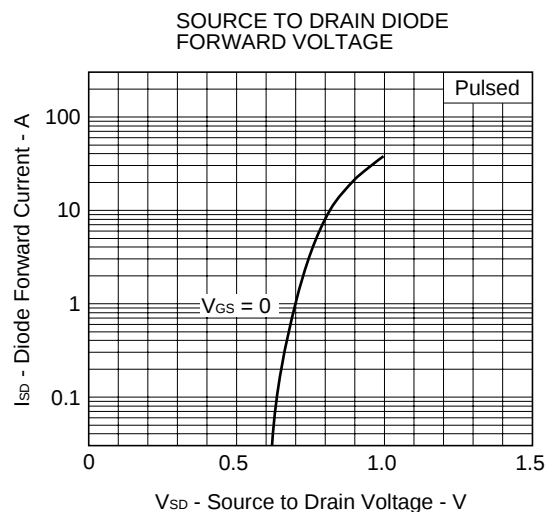
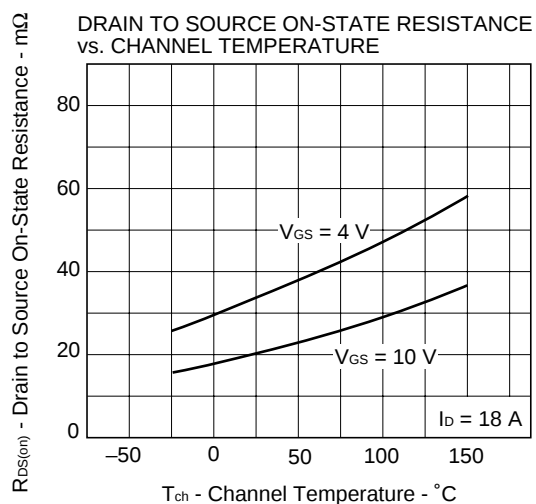


DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



GATE TO SOURCE CUTOFF VOLTAGE vs. CHANNEL TEMPERATURE





## REFERENCE

| Document Name                                                  | Document No. |
|----------------------------------------------------------------|--------------|
| NEC semiconductor device reliability/quality control system.   | TEI-1202     |
| Quality grade on NEC semiconductor devices.                    | IEI-1209     |
| Semiconductor device mounting technology manual.               | C10535E      |
| Semiconductor device package manual.                           | C10943X      |
| Guide to quality assurance for semiconductor devices.          | MEI-1202     |
| Semiconductor selection guide.                                 | X10679E      |
| Power MOS FET features and application switching power supply. | TEA-1034     |
| Application circuits using Power MOS FET.                      | TEA-1035     |
| Safe operating area of Power MOS FET.                          | TEA-1037     |

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Anti-radioactive design is not implemented in this product.